

ABSTRACT OF DISCLOSURE

5 A semiconductor device including an NMOSFET
which has an n-type source/drain main region containing
arsenic and an n-type source/drain buffer region having
arsenic and phosphorous of which a concentration is
lower than that of the source/drain main region, and the
10 concentration of the phosphorous in the source/drain
buffer region is smaller than the concentration of the
arsenic therein. The semiconductor device has a
suppressed reverse short channel effect and reduced p-n
junction leakage current. Further, the semiconductor
15 device has a larger margin to a certain gate length and a
specified threshold voltage to elevate a production yield.